

**In the Claims:**

1-6. (cancelled)

7. (original) An integrated circuit structure, comprising:

a gate structure formed on a body of semiconductor material;

an insulating layer formed opposite said gate structure beneath said semiconductor material;

a conducting region within said insulating layer beneath said gate structure, said conducting region having sublithographic width.

8. (original) The integrated circuit of Claim 7, wherein said conducting region contacts said semiconductor material.

9. (original) The integrated circuit of Claim 7, wherein said conducting region is formed in a trench with sidewalls.

10. (original) The integrated circuit of Claim 7, wherein said semiconductor material is silicon.

11. (original) The integrated circuit of Claim 7, wherein said conducting region is separated from said semiconductor material by a dielectric material.

12 - 29. (Withdrawn)